

L Number	Hits	Search Text	DB	Time stamp
24	2	6713347.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 17:20
25	0	6713347.URPN.	USPAT	2004/10/29 17:18
26	18	("5182719" "5600164" "5663084" "5668035" "5768194" "5834352" "5861347" "5888869" "5910016" "5926729" "5989948" "6017797" "6087225" "6133164" "6165849" "6165918" "6228721" "6261978").PN.	USPAT	2004/10/29 17:18
27	12	((("5182719" "5600164" "5663084" "5668035" "5768194" "5834352" "5861347" "5888869" "5910016" "5926729" "5989948" "6017797" "6087225" "6133164" "6165849" "6165918" "6228721" "6261978").PN.) and (high adj voltage)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 17:20
28	7	((("5182719" "5600164" "5663084" "5668035" "5768194" "5834352" "5861347" "5888869" "5910016" "5926729" "5989948" "6017797" "6087225" "6133164" "6165849" "6165918" "6228721" "6261978").PN.) and (high adj voltage)) and (low adj voltage)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 17:27
29	8279	form\$3 with first with ion with implant\$5 with layer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 17:28
30	540	implant\$5 with high with voltage with well	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 18:12
31	7063	form\$3 with second with ion with implant\$5 with layer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 17:29
32	2049	remov\$3 with second with first with ion with implant\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 17:29
33	24	(form\$3 with first with ion with implant\$5 with layer) and (implant\$5 with high with voltage with well) and (form\$3 with second with ion with implant\$5 with layer) and (remov\$3 with second with first with ion with implant\$5)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 18:12
34	18	((form\$3 with first with ion with implant\$5 with layer) and (implant\$5 with high with voltage with well) and (form\$3 with second with ion with implant\$5 with layer) and (remov\$3 with second with first with ion with implant\$5)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 18:13
35	320	implant\$5 with low with voltage with well	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 18:12
36	35	(form\$3 with first with ion with implant\$5 with layer) and (implant\$5 with high with voltage with well) and (form\$3 with second with ion with implant\$5 with layer) and (implant\$5 with low with voltage with well)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 18:12

37	22	((form\$3 with first with ion with implant\$5 with layer) and (implant\$5 with high with voltage with well) and (form\$3 with second with ion with implant\$5 with layer) and (implant\$5 with low with voltage with well)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 18:13
38	17	((form\$3 with first with ion with implant\$5 with layer) and (implant\$5 with high with voltage with well) and (form\$3 with second with ion with implant\$5 with layer) and (implant\$5 with low with voltage with well)) and (@ad<20020222 or @rlad<20020222)) not (((form\$3 with first with ion with implant\$5 with layer) and (implant\$5 with high with voltage with well) and (form\$3 with second with ion with implant\$5 with layer) and (remov\$3 with second with first with ion with implant\$5)) and (@ad<20020222 or @rlad<20020222))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 18:13
-	3203	438/22\$1.cccls. or 438/518.cccls. or 438/519.cccls. or 438/527.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 17:17
-	18	(438/22\$1.cccls. or 438/518.cccls. or 438/519.cccls. or 438/527.cccls.) and (high with voltage with (n adj well)) and (low with voltage with (p adj well))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 17:46
-	1	(sixth adj mask\$3) and (high with voltage with (n adj well)) and (low with voltage with (p adj well))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:21
-	70	(438/22\$1.cccls. or 438/518.cccls. or 438/519.cccls. or 438/527.cccls.) and (high with voltage with well) and (low with voltage with well)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 18:40
-	68	((438/22\$1.cccls. or 438/518.cccls. or 438/519.cccls. or 438/527.cccls.) and (high with voltage with well) and (low with voltage with well)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 17:47
-	324	(high with voltage with well) and (first with low with voltage with well) and (second with low with voltage with well)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 19:55
-	39	((high with voltage with well) and (first with low with voltage with well) and (second with low with voltage with well)) and (implant\$5 with (p adj (body or region or well)))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 19:29
-	0	20030162375.URPN.	USPAT	2003/12/15 18:43
-	44	257/548.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 19:13
-	35	((high with voltage with well) and (first with low with voltage with well) and (second with low with voltage with well)) and (implant\$5 with p with high with voltage)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 19:29
-	7	((first with mask\$3) same (implant\$5 with high with voltage with well)) and ((second with mask\$3) same (first with low with voltage with well))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/15 19:57
-	2579	high with voltage with well with (implant\$5 or form\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:22

	201	low with voltage with well with (implant\$5 or form\$3) with first	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:23
	196	low with voltage with well with (implant\$5 or form\$3) with second	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:23
	114	(high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and (low with voltage with well with (implant\$5 or form\$3) with second)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:23
	3208	438/22\$1.cccls. or 438/518.cccls. or 438/519.cccls. or 438/527.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 11:24
	11	((high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and (low with voltage with well with (implant\$5 or form\$3) with second)) and (438/22\$1.cccls. or 438/518.cccls. or 438/527.cccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 12:52
	6	((high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and (low with voltage with well with (implant\$5 or form\$3) with second)) and cmos and dmos	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 12:42
	7	((high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and cmos and dmos	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 14:16
	8	((high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and (low with voltage with well with (implant\$5 or form\$3) with second)) and (fifth with mask\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 14:16
	144	((high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 13:13
	131	((high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 13:13
	1	((high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and (low with voltage with well with (implant\$5 or form\$3) with second)) and (fifth with photoresist with film)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 19:53
	1	((high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and photodiode and mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 19:55
	5	((high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 19:58
	21	((high with voltage with well with (implant\$5 or form\$3)) and (low with voltage with well with (implant\$5 or form\$3) with first) and photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 19:59

-	1	((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3)) and photodiode and mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 20:04
-	3	((high with voltage with well with (implant\$5 or form\$3))) and (low with voltage with well with (implant\$5 or form\$3)) and mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 20:10
-	21	(high with voltage with well) and (low with voltage with well) and mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:35
-	1	(high adj voltage adj well) and (low adj voltage adj well) and mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 20:11
-	2	cmos same dmos same mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:04
-	10	cmos and dmos and mems	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:05
-	2420	mem same (accelerometer or sensor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:03
-	2420	mems same (accelerometer or sensor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:03
-	1862	mems with (accelerometer or sensor)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:03
-	509	mems with accelerometer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:03
-	2	cmos same dmos same photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:18
-	16	cmos and dmos and photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:05
-	31	cmos same dmos same soi	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:18
-	2	5578506.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:30
-	2	5681761.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:30
-	113	(high with voltage with well) and (low with voltage with well) and photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:36
-	104	((high with voltage with well) and (low with voltage with well) and photodiode) and @ad<20020222	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:47
-	1	(high adj voltage adj well) and (low adj voltage adj well) and photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:37

	71986	photodiode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:48
	67	photodiode and dmos	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/12/16 21:48
	35	(implant\$5 with high with voltage with well) and (implant\$5 with low with voltage with well) and (first adj mask) and (second adj mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/25 17:04
	28	(implant\$5 with high with voltage with well) and (implant\$5 with low with voltage with well) and (first adj mask) and (second adj mask) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/25 17:07
	0	((implant\$5 with high with voltage with well) same (first adj protective)) and ((implant\$5 with low with voltage with well) same (second adj protective)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 14:23
	0	((implant\$5 with high with voltage with well) same (first adj oxide)) and ((implant\$5 with low with voltage with well) same (second adj oxide)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 14:23
	0	((implant\$5 with high with voltage with well) same (first with protective)) and ((implant\$5 with low with voltage with well) same (second with protective)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 15:48
	8	((implant\$5 with high with voltage with well) same (first with oxide)) and ((implant\$5 with low with voltage with well) same (second with oxide)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 14:41
	152	((implant\$5 with high with voltage with well) same (implant\$5 with low with voltage with well)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 14:28
	77	((implant\$5 with high with voltage with well) same (implant\$5 with low with voltage with well)) and (@ad<20020222 or @rlad<20020222)) and 438/\$3.cc1s.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 14:28
	7	(implant\$5 with high with voltage with well with first with mask) and (implant\$5 with low with voltage with well with second with mask) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 14:42
	3	((high with voltage with well) same (first with protective)) and ((low with voltage with well) same (second with protective)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 15:50
	18	((high with voltage with well) same (first with mask)) and ((low with voltage with well) same (second with mask)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 16:46
	30	((high with voltage with well) same (first with oxide)) and ((low with voltage with well) same (second with oxide)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 17:38
	54	((high with voltage with implant\$5) same (first with mask)) and ((low with voltage with implant\$5) same (second with mask)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/25 17:37

-	0	(implant\$5 with high with voltage with well) and ((low with voltage with well) same (remov\$3 with second with portion with first with mask)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 17:40
-	44	(high with voltage with well) and (low with voltage with well) and (remov\$3 with second with portion with first with mask) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 18:16
-	867	(438/200.ccls. or 438/279.ccls.) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 18:17
-	205	((438/200.ccls. or 438/279.ccls.) and (@ad<20020222 or @rlad<20020222)) and (high with voltage) and (low with voltage)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 18:17
-	159	((438/200.ccls. or 438/279.ccls.) and (@ad<20020222 or @rlad<20020222)) and (high with voltage) and (low with voltage)) and mask\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/06/29 18:18
-	0	wo200237547	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/12 10:56
-	1	"wo 200237547"	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/12 10:58
-	4	985447.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/07/12 10:58
-	8	(implant\$5 with (high adj voltage adj well)) and (implant\$5 with (low adj voltage adj well))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/25 20:05
-	4	((implant\$5 with (high adj voltage adj well)) and (implant\$5 with (low adj voltage adj well))) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/25 17:10
-	10	(implant\$5 same (high adj voltage adj well)) and (implant\$5 same (low adj voltage adj well))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/25 17:09
-	6	((implant\$5 same (high adj voltage adj well)) and (implant\$5 same (low adj voltage adj well))) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/25 17:15
-	2	((implant\$5 same (high adj voltage adj well)) and (implant\$5 same (low adj voltage adj well))) and (@ad<20020222 or @rlad<20020222)) not ((implant\$5 with (high adj voltage adj well)) and (implant\$5 with (low adj voltage adj well))) and (@ad<20020222 or @rlad<20020222))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/25 17:10
-	26	(high adj voltage adj well) same (low adj voltage adj well)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/25 17:23
-	20	((high adj voltage adj well) same (low adj voltage adj well)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/25 20:14
-	27	(high adj voltage adj well) and (low adj voltage adj well) and implant\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/25 17:23

-	21	((high adj voltage adj well) and (low adj voltage adj well) and implant\$5) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/25 17:24
-	8	((high adj voltage adj well) and (low adj voltage adj well) and implant\$5) and (@ad<20020222 or @rlad<20020222)) not (((high adj voltage adj well) same (low adj voltage adj well)) and (@ad<20020222 or @rlad<20020222))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/25 17:24
-	58	((high with voltage with implant\$5) same (first with mask\$3)) and ((low with voltage with implant\$5) same (second with mask\$3)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/25 20:00
-	58	((high with voltage with implant\$5) same (first with mask\$3)) and ((low with voltage with implant\$5) same (second with mask\$3)) and (@ad<20020222 or @rlad<20020222)) not (((high adj voltage adj well) and (low adj voltage adj well) and implant\$5) and (@ad<20020222 or @rlad<20020222))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/25 17:38
-	13	((high with voltage) same implant\$5 same (low with voltage) same (partial\$2 with mask\$3)) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/25 20:01
-	541	(implant\$5 with (high adj voltage)) and (implant\$5 with (low adj voltage))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/25 20:12
-	212	((implant\$5 with (high adj voltage)) same mask\$3) and ((implant\$5 with (low adj voltage)) same mask\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/25 20:14
-	135	((implant\$5 with (high adj voltage)) same mask\$3) and ((implant\$5 with (low adj voltage)) same mask\$3)) and 438/\$3.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/25 20:14
-	119	((((implant\$5 with (high adj voltage)) same mask\$3) and ((implant\$5 with (low adj voltage)) same mask\$3)) and 438/\$3.ccls.) and (@ad<20020222 or @rlad<20020222)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/10/29 17:30